PBSS5160T



60 V, 1 A PNP low V_{CEsat} (BISS) transistor Rev. 04 — 15 January 2010

Product data sheet

Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4160T.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency due to less heat generation
- Reduces Printed-Circuit Board (PCB) area required
- Cost-effective replacement for medium power transistors BCP52 and BCX52

1.3 Applications

- Major application segments:
 - Automotive
 - ◆ Telecom infrastructure
 - Industrial
- Power management:
 - DC-to-DC conversion
 - Supply line switching
- Peripheral driver:
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - ◆ Inductive load drivers (e.g. relays, buzzers and motors)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-60	V
I _C	collector current		-	-	-1	Α
I _{CM}	peak collector current	t = 1 ms or limited by $T_{j(max)}$	-	-	-2	Α
R _{CEsat}	collector-emitter saturation resistance	$I_C = -1 A;$ $I_B = -100 \text{ mA}$	<u>[1]</u> _	220	330	mΩ

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.



2. Pinning information

Table 2. Pinning

Table 2.	i iiiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	3	3
3	collector	1 2	1—
			006aab25

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5160T	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBSS5160T	*U6

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-80	V
V_{CEO}	collector-emitter voltage	open base	-	-60	V
V_{EBO}	emitter-base voltage	open collector	-	- 5	V
I _C	collector current		<u>[1]</u> _	-0.9	Α
			[2] _	-1	Α
I _{CM}	peak collector current	t = 1 ms or limited by $T_{j(max)}$	-	-2	Α
I _B	base current		-	-300	mA
I _{BM}	peak base current	$t_p \leq 300~\mu\text{s};~\delta \leq 0.02$	-	-1	Α

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

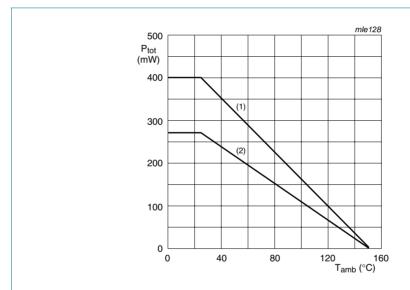
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Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} \leq 25 ^{\circ}C$	[1] _	270	mW
			[2] _	400	mW
			[1][3]	1.25	W
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Operated under pulse conditions: duty cycle $\delta \le$ 20 %, pulse width $t_p \le$ 10 ms.



- (1) FR4 PCB, mounting pad for collector 1 cm²
- (2) FR4 PCB, standard footprint

Fig 1. Power derating curves

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	<u>[1]</u> -	-	465	K/W
	junction to ambient		[2] _	-	312	K/W
			[1][3]	-	100	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Operated under pulse conditions: duty cycle $\delta \le 20$ %, pulse width $t_p \le 10$ ms.

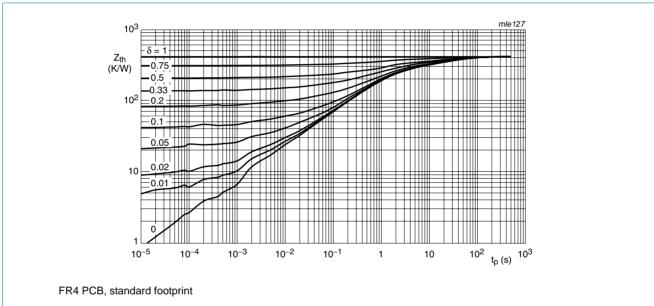


Fig 2. Transient thermal impedance as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

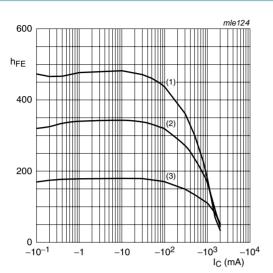
 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}		$V_{CB} = -60 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
current		$V_{CB} = -60 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -60 \text{ V}; V_{BE} = 0 \text{ V}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}$					
		$I_C = -1 \text{ mA}$		200	350	-	
		$I_C = -500 \text{ mA}$	[1]	150	250	-	
		$I_C = -1 A$	[1]	100	160	-	
V _{CEsat} collector-emitter saturation voltag		$I_C = -100 \text{ mA}; I_B = -1 \text{ mA}$		-	-110	-160	mV
	saturation voltage	$I_C = -500 \text{ mA};$ $I_B = -50 \text{ mA}$		-	-120	–175	mV
		$I_C = -1 \text{ A}; I_B = -100 \text{ mA}$	[1]	-	-220	-330	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = -1 A$; $I_B = -100 \text{ mA}$	[1]	-	220	330	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_C = -1 A$; $I_B = -50 \text{ mA}$		-	-0.95	-1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ A}$		-	-0.82	-0.9	V
f _T	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{C} = -50 \text{ mA}; f = 100 \text{ MHz}$		150	220	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	9	15	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

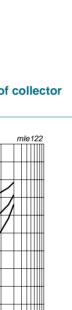
-1.2

 V_{BE}

-0.8

-0.4

Fig 3. DC current gain as a function of collector current; typical values





(1)
$$T_{amb} = -55 \, ^{\circ}C$$

 -10^{-1}

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values

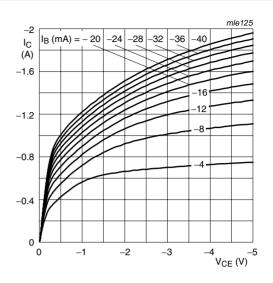
 -10^{2}

-10

 -10^{3}

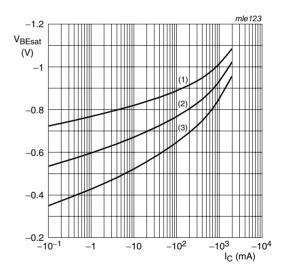
 -10^{4}

I_C (mA)



T_{amb} = 25 °C

Fig 4. Collector current as a function of collector-emitter voltage; typical values



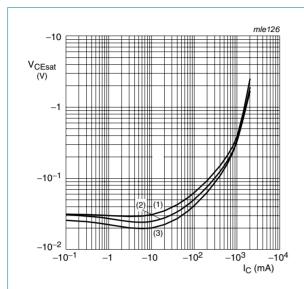
 $I_{\rm C}/I_{\rm B}=20$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values



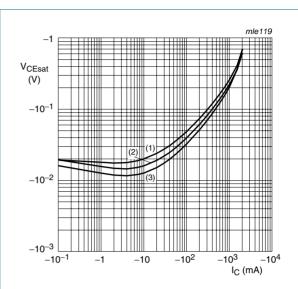
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



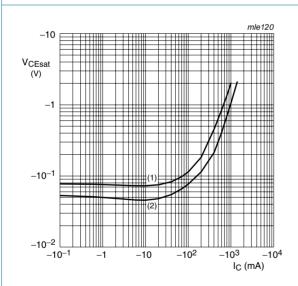
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

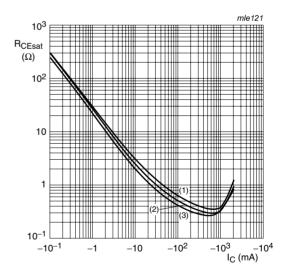
Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

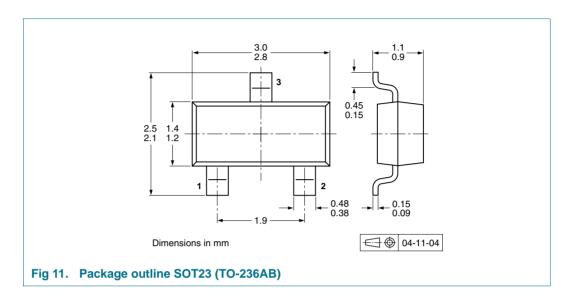
(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

8. Package outline



9. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PBSS5160T	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 12.

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10. Revision history

Table 9. Revision history

Nexperia

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5160T_4	20100115	Product data sheet	-	PBSS5160T_N_3		
Modifications:		of this data sheet has been re	edesigned to comply w	rith the new identity		
	 Legal texts have been adapted to the new company name where appropriate. 					
	• Table 1 "Qui	ck reference data": amended				
	 Section 4 "M 	arking": amended				
	• Figure 4: updated					
	 Figure 11: superseded by minimized package outline drawing 					
	 Section 9 "Packing information": added 					
	 Section 11 "L 	<u>egal information"</u> : updated				
PBSS5160T_N_3	20080718	Product data sheet	-	PBSS5160T_2		
PBSS5160T_2	20040527	Product specification	-	PBSS5160T_1		
PBSS5160T_1	20030623	Product specification	-	-		

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11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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